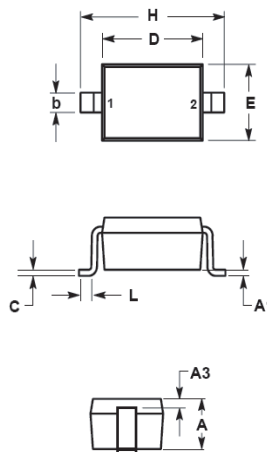


### Features

- High Breakdown Voltage.
- Low Turn-on Voltage.
- Guard Ring Construction for Transient.
- Marking Code: S9



SOD-323		
Dim.	Min.	Max.
A	0.80	1.10
A1	0.00	0.10
A3	0.15 REF	
B	0.25	0.40
C	0.10	0.15
D	1.60	1.80
E	1.15	1.35
L	0.20	0.50
H	2.30	2.80
Dimensions in millimeter		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	100	V
Reverse Voltage	$V_R$	100	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Non-repetitive Peak Forward Surge Current at $t = 8.3 \text{ ms}$	$I_{FSM}$	750	mA
Power Dissipation	$P_{tot}$	200	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	500	$^\circ\text{C/W}$
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

### Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

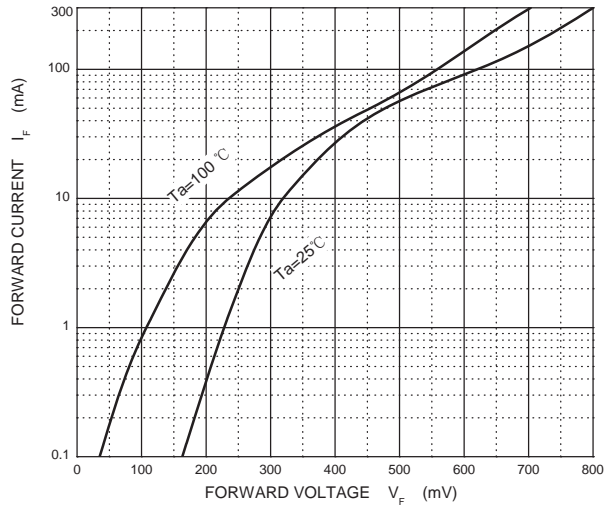
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage(Note 2)	$V_R$	$I_R = 100 \mu\text{A}$	100			V
Reverse voltage leakage current	$I_R$	$V_{R1} = 1.5\text{V}$			0.3	$\mu\text{A}$
		$V_{R2} = 10\text{V}$			0.5	
		$V_{R3} = 50\text{V}$			1	
		$V_{R4} = 75\text{V}$			2	
Forward voltage(Note 2)	$V_F$	$I_{F1} = 0.1\text{mA}$			0.25	V
		$I_{F2} = 10\text{mA}$			0.45	
		$I_{F3} = 250\text{mA}$			1	
Diode capacitance	$C_T$	$V_R = 0, f = 1\text{MHz}$		20		pF
		$V_R = 1\text{V}, f = 1\text{MHz}$		12		

Notes: 1. Part mounted on FR-4 board with recommended pad layout.

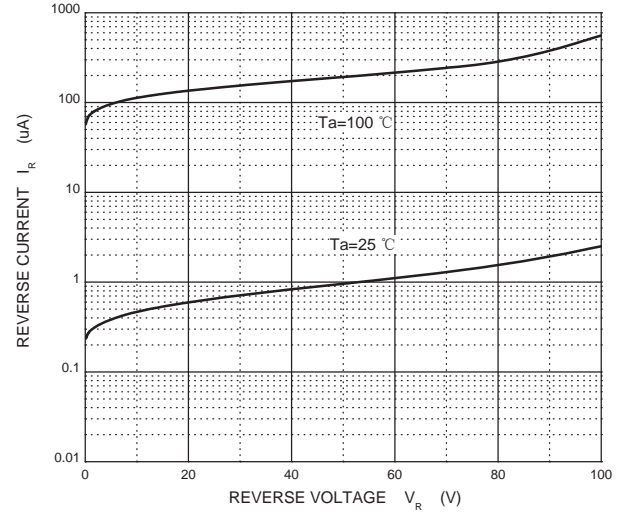
2. Short dura on pulse test used to minimize self-heating effect.

### TYPICAL TRANSIENT CHARACTERISTICS

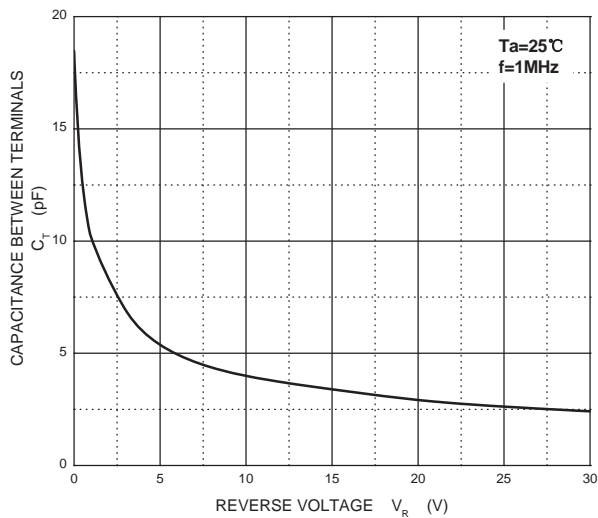
Forward Characteristics



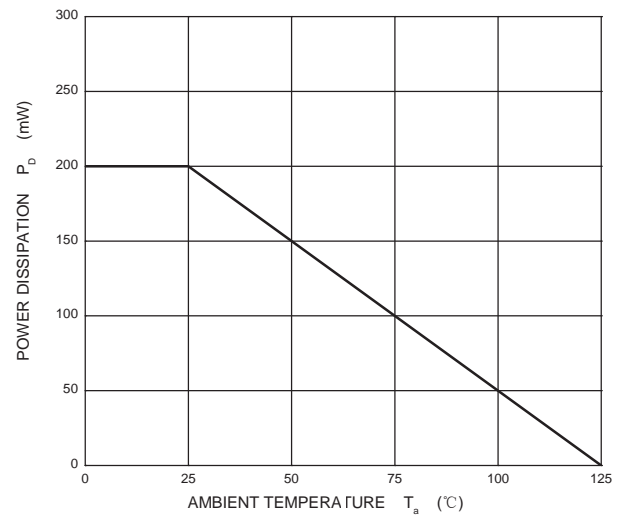
Reverse Characteristics



Capacitance Characteristics



Power Derating Curve



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## IMPORTANT NOTICE

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